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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.009			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.013			
I _D (A)	50			
Configuration	Single			

Top View

Lead (Pb)-free and Halogen-free

TO-220

FEATURES

SQP50N06-09L-GE3

- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- AEC-Q101 Qualifiedd
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



HALOGEN

FREE

UUU GDS	N-Channel MOSFET	
ORDERING INFORMATION		
Package		TO-220

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V _{GS}	± 20	V
Continuous Drain Current	T _C = 25 °C ^a	- I _D	50	
Continuous Drain Current	T _C = 125 °C		49	
Continuous Source Current (Diode Conduction) ^a		I _S	50	Α
Pulsed Drain Current ^b		I _{DM}	200	
Single Pulse Avalanche Current	1 04 mil	I _{AS}	48	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	115	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	D	136	W
	T _C = 125 °C	P_{D}	45	VV
Operating Junction and Storage Temperatu	re Range	T _J , T _{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	50	°C/W	
Junction-to-Case (Drain)		R _{thJC}	1.1	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	1			L	L	L	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nΑ
		V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	250	1
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α
		V _{GS} = 10 V	I _D = 20 A	-	0.0071	0.0090	Ω
Drain Course On State Besistance	В	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0160	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0190	
		V _{GS} = 4.5 V	I _D = 10 A	-	0.0094	0.0130	
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		-	62	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	2451	3065	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	435	545	
Reverse Transfer Capacitance	C _{rss}			-	192	240	
Total Gate Charge ^c	Qg			-	48	72	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 50 \text{ A}$	-	7.1	-	nC
Gate-Drain Charge ^c	Q_{gd}	1		-	13.5	-	
Gate Resistance	R_g	f = 1 MHz		0.85	1.7	2.6	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	10	15	
Rise Time ^c	t _r	V_{DD} = 30 V, R_L = 0.6 Ω $I_D \cong$ 50 A, V_{GEN} = 10 V, R_g = 1 Ω		-	11	17	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	27	41	
Fall Time ^c	t _f			-	8	12	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	200	Α
Forward Voltage	V_{SD}	I _F = 20 A, V _{GS} = 0 V		_	0.82	1.5	V

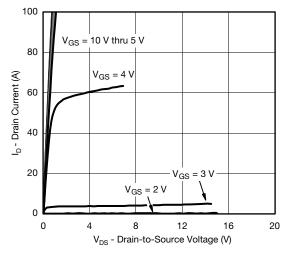
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

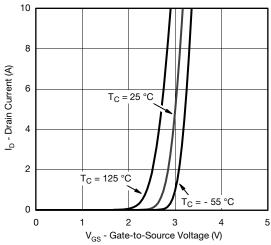
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



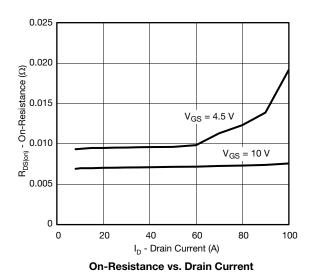
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

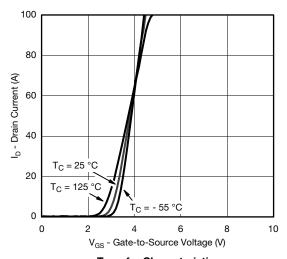


Output Characteristics

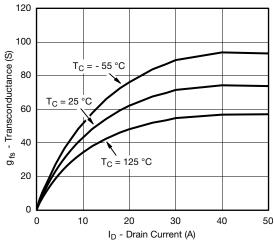


Transfer Characteristics

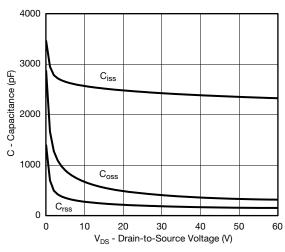




Transfer Characteristics



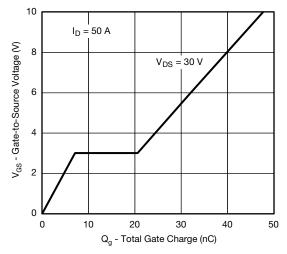
Transconductance



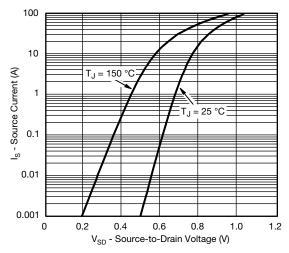
Capacitance



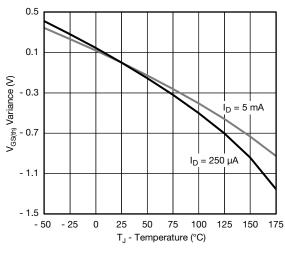
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



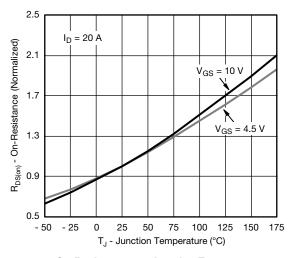
Gate Charge



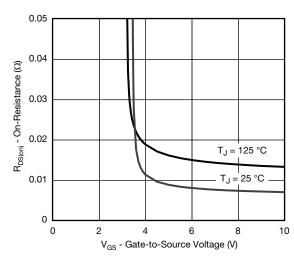
Source Drain Diode Forward Voltage



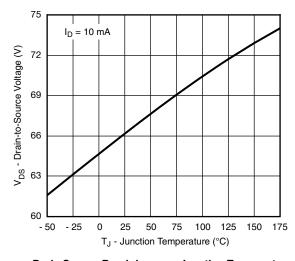
Threshold Voltage



On-Resistance vs. Junction Temperature



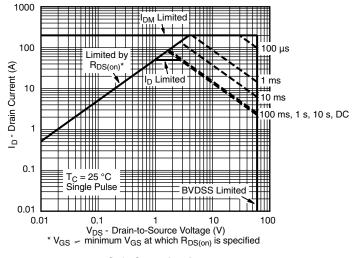
On-Resistance vs. Gate-to-Source Voltage



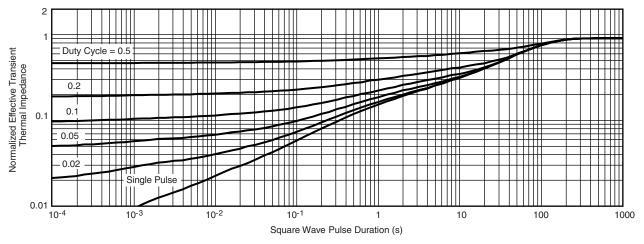
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



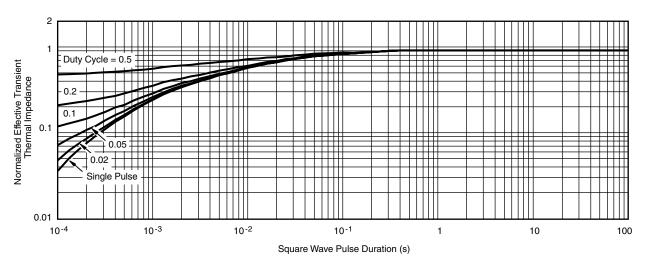
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

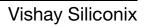


Normalized Thermal Transient Impedance, Junction-to-Case

Note

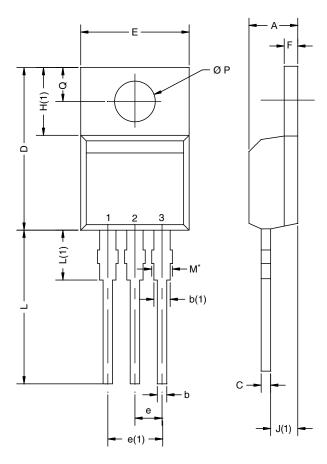
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62664.





TO-220AB



	D2

	MILLIN	IETERS	INC	HES		
DIM.	MIN.	MAX.	MIN.	MAX.		
А	4.25	4.65	0.167	0.183		
b	0.69	1.01	0.027	0.040		
b(1)	1.20	1.73	0.047	0.068		
С	0.36	0.61	0.014	0.024		
D	14.85	15.49	0.585	0.610		
D2	12.19	12.70	0.480	0.500		
Е	10.04	10.51	0.395	0.414		
е	2.41	2.67	0.095	0.105		
e(1)	4.88	5.28	0.192	0.208		
F	1.14	1.40	0.045	0.055		
H(1)	6.09	6.48	0.240	0.255		
J(1)	2.41	2.92	0.095	0.115		
L	13.35	14.02	0.526	0.552		
L(1)	3.32	3.82	0.131	0.150		
ØΡ	3.54	3.94	0.139	0.155		
Q	2.60	3.00	0.102	0.118		
ECN: T14-0413-Rev. P, 16-Jun-14 DWG: 5471						

Note

Revison: 16-Jun-14 1 Document Number: 71195

 $^{^{\}star}$ M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM

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